Central™
Semiconductor Corp.

PROCESS CPS130

Silicon Controlled Rectifier

16 Amp Sensitive Gate SCR Chip

PROCESS DETAILS

Process	Glass Passivated Mesa
Die Size	130 x 130 MILS
Die Thickness	8.7 MILS
Cathode Bonding Pad Area	99 x 49 MILS
Gate Bonding Pad Area	42 x 42 MILS
Top Side Metalization	Al - 45,000Å
Back Side Metalization	Al/Mo/Ni/Ag - 32,000Å

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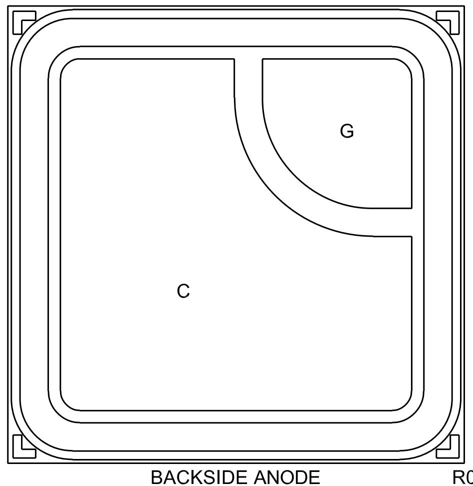
GEOMETRY



GROSS DIER PER 4 INCH WAFER
624

PRINCIPAL DEVICE TYPES
CS220-16M Series
CSDD-16M Series

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